NPN Silicon Power Transistor

This device is designed for use in switching regulators and motor control.

Features

- Low Collection Emitter Saturation Voltage
- Fast Switching Speed
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Sustaining Voltage	V _{CEO}	120	Vdc
Collector-Emitter Breakdown Voltage	V _{CBO}	240	Vdc
Emitter-Base Voltage	V _{EBO}	7.0	Vdc
Collector Current – Continuous	۱ _C	12	Adc
Collector Current – Peak (Note 1)	I _{CM}	20	Adc
Base Current	Ι _Β	4.0	Adc
Total Device Dissipation ($T_C = 25^{\circ}C$) Derate above $25^{\circ}C$	P _D	70 0.56	W W/∘C
Operating and Storage Temperature	T _J , T _{stg}	– 65 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle \leq 10%.

THERMAL CHARACTERISTICS

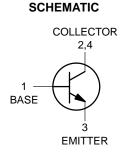
Rating	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient	$R_{ hetaJC} \ R_{ hetaJA}$	1.78 62.5	°C/W

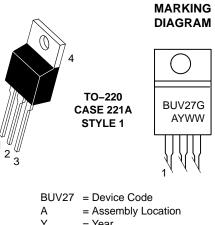


ON Semiconductor®

www.onsemi.com

POWER TRANSISTOR 12 AMPERES 120 VOLTS 70 WATTS





	/
Y	= Year
WW	= Work Week
G	= Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
BUV27G	TO–220 (Pb–Free)	50 per Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BUV27

ELECTRICAL CHARACTERISTICS ($T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
I _{CER}	Collector Cut–off Current ($R_{BE} = 50 \Omega$)	$V_{CE} = 240 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$			3.0	mA
I _{CEX}	Collector Cut-off Current	V_{CE} = 240 V, V_{BE} = -1.5 V, T_{C} = 125°C			1.0	mA
I _{EBO}	Emitter Cut–off Current ($I_C = 0$)	V _{BE} = 5 V			1.0	mA
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage	I _C = 0.2 A, L = 25 mH	120			V
V _{EBO}	Emitter–Base Voltage ($I_C = 0$)	I _E = 50 mA	7.0		30	V
V _{CE(sat)} (Note 2)	Collector-Emitter Saturation Voltage				0.7 1.5	V
V _{BE(sat)} (Note 2)	Base–Emitter Saturation Voltage	I _C = 8 A, I _B = 0.8 A			2.0	V

Resistive Load

Inductive Load

t _s t _f	Storage Time Fall Time	$V_{CC} = 90 \text{ V}, I_C = 8 \text{ A}$ $I_{B1} = 0.8 \text{ A}, V_{BE} = -5 \text{ V}$	0.6 0.04		μs
t _s t _f	Storage Time Fall Time	$\begin{array}{l} L_{B} = 1 \ \mu H \\ V_{CC} = 90 \ V, \ I_{C} = 8 \ A \\ I_{B1} = 0.8 \ A, \ V_{BE} = -5 \ V \\ L_{B} = 1 \ \mu H, \ T_{J} = 125^{\circ}C \end{array}$		2.0 0.15	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
Pulsed: Pulse Duration = 300 μs, Duty Cycle = 2%

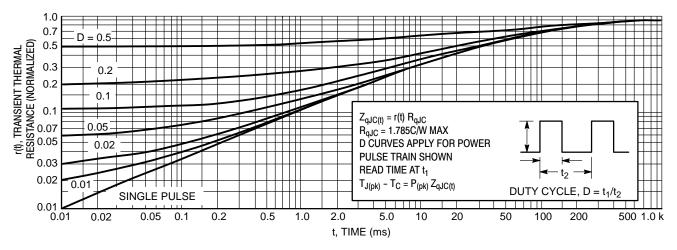


Figure 1. Thermal Response

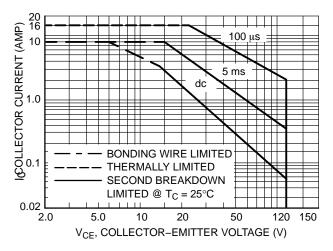


Figure 2. Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation then the curves indicate.

The data of Figures 2 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^{\circ}$ C. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

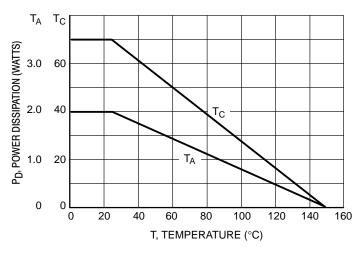
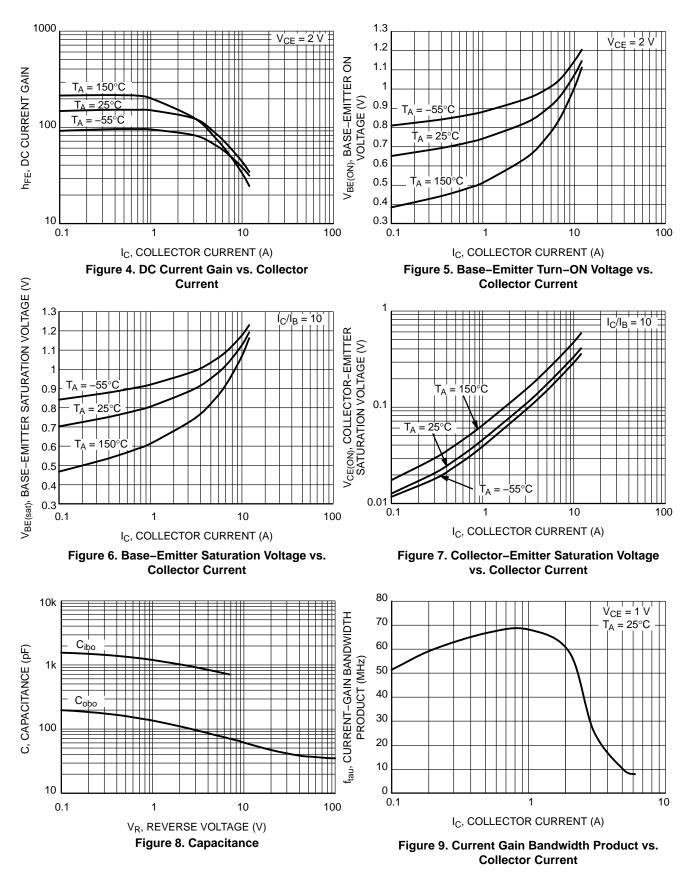


Figure 3. Power Derating

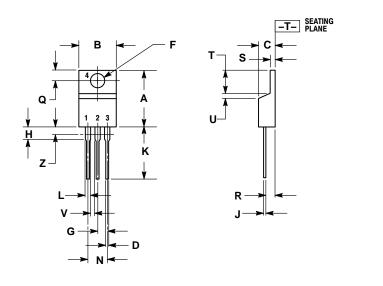
BUV27



BUV27

PACKAGE DIMENSIONS

TO-220 CASE 221A-09 ISSUE AH



NOTES:

 DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: INCH.

 DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INC	HES	MILLIMETER		
DIM	MIN	MAX	MIN	MAX	
Α	0.570	0.620	14.48	15.75	
В	0.380	0.415	9.66	10.53	
С	0.160	0.190	4.07	4.83	
D	0.025	0.038	0.64	0.96	
F	0.142	0.161	3.61	4.09	
G	0.095	0.105	2.42	2.66	
Н	0.110	0.161	2.80	4.10	
ſ	0.014	0.024	0.36	0.61	
κ	0.500	0.562	12.70	14.27	
Г	0.045	0.060	1.15	1.52	
Ν	0.190	0.210	4.83	5.33	
Q	0.100	0.120	2.54	3.04	
R	0.080	0.110	2.04	2.79	
S	0.045	0.055	1.15	1.39	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
۷	0.045		1.15		
Ζ		0.080		2.04	

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR

ON Semiconductor and the 🛄 are registered trademarks of Semiconductor Components Industries, LLC (SCILLC) or its subsidiaries in the United States and/or other countries. SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdt/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application. Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regardi

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303–675–2175 or 800–344–3860 Toll Free USA/Canada Fax: 303–675–2176 or 800–344–3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support:

Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81–3–5817–1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ON Semiconductor: BUV27G